

Docket No.: M4065.0909/P909-A
(PATENT)

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Patent Application of:
Li Li, et al.

Application No.: Not Yet Assigned

Filed: December 12, 2003

Art Unit: 2823

For: METHOD FOR FILLING VIA WITH
METAL

Examiner: Thanh V. Pham

INFORMATION DISCLOSURE STATEMENT (IDS)

Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

Dear Sir:

Pursuant to 37 CFR 1.56, 1.97 and 1.98, the attention of the Patent and Trademark Office is hereby directed to the references listed on the attached PTO/SB/08. It is respectfully requested that the information be expressly considered during the prosecution of this application, and that the references be made of record therein and appear among the "References Cited" on any patent to issue therefrom.

This Information Disclosure Statement accompanies the new patent application submitted herewith.

Those patents or publications which are marked with an asterisk (*) next to the Cite No. in the attached form PTO/SB/08 are not supplied because they were previously cited by or submitted to the Office in a prior application number 10/388,264, filed March 14, 2003 and relied upon in this application for an earlier filing date under 35 U.S.C. 120.

Application No.: Not Yet Assigned

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The Director is hereby authorized to charge any deficiency in the fees filed, asserted to be filed or which should have been filed herewith (or with any paper hereafter filed in this application by this firm) to our Deposit Account No. 04-1073, under Order No. M4065.0909/P909-A.

Dated: January 16, 2004

Respectfully submitted,

By 

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Substitute for form 1449A/PTO INFORMATION DISCLOSURE STATEMENT BY APPLICANT <i>(use as many sheets as necessary)</i>				Complete if Known	
				Application Number	Not Yet Assigned
				Filing Date	October 29, 2003
				First Named Inventor	Li Li
				Art Unit	Not Yet Assigned
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Sheet	1	of	11	Attorney Docket Number	M4065.0909/P909-A

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		Country Code ³ -Number ⁴ -Kind Code ⁵ (if known)				
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Sheet	4	of	11	Attorney Docket Number	M4065.0909/P909-A

OTHER PRIOR ART – NON PATENT LITERATURE DOCUMENTS				
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		Filing Date	March 13, 2003
		First Named Inventor	Li Li
		Group Art Unit	Not Yet Assigned
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